

L Number	Hits	Search Text	DB	Time stamp
2	13	5163180.pn. 6515931.pn. 6326651.pn. 6545926.pn. 6518614.pn. 5946575.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 13:13
3	30	(antifuse or anti-fuse or antifusing or anti-fusing or anti-fusible or antifusible or one adj time adj programmable) with (mosfet or mos or fet) and (source near2 extension or drain near2 extension or ldd or lightly near doped near drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 13:25
4	53	(gate near (oxide or dielectric)) near2 (breakdown or rupture or ruptured or rupturing) with (mosfet or mos or fet) and (source near2 extension or drain near2 extension or ldd or lightly near doped near drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 13:26
5	246	(gate near (oxide or dielectric)) near2 (breakdown or rupture or ruptured or rupturing) and (mosfet or mos or fet) and (source near2 extension or drain near2 extension or ldd or lightly near doped near drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 13:44
6	107	(gate near (oxide or dielectric)) near2 (breakdown or rupture or ruptured or rupturing) and (mosfet or mos or fet) and (source near2 extension or drain near2 extension or ldd or lightly near doped near drain) and (fuse or antifuse or fusible or programmable or memory or programming)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 13:45